

A perspective view of a semiconductor device 1. The device consists of a substrate 3 with a top surface layer 9. On the surface layer 9, there are several rectangular regions: 6a, 6b, 6d, 6e, 8(8A), 8(8B), 8bk, 7, Gd, Gk, Gn, g, Q, 10, 11, and 12. A cross-section Z-Z' is shown, indicating the internal structure of the device.

FIG. 2

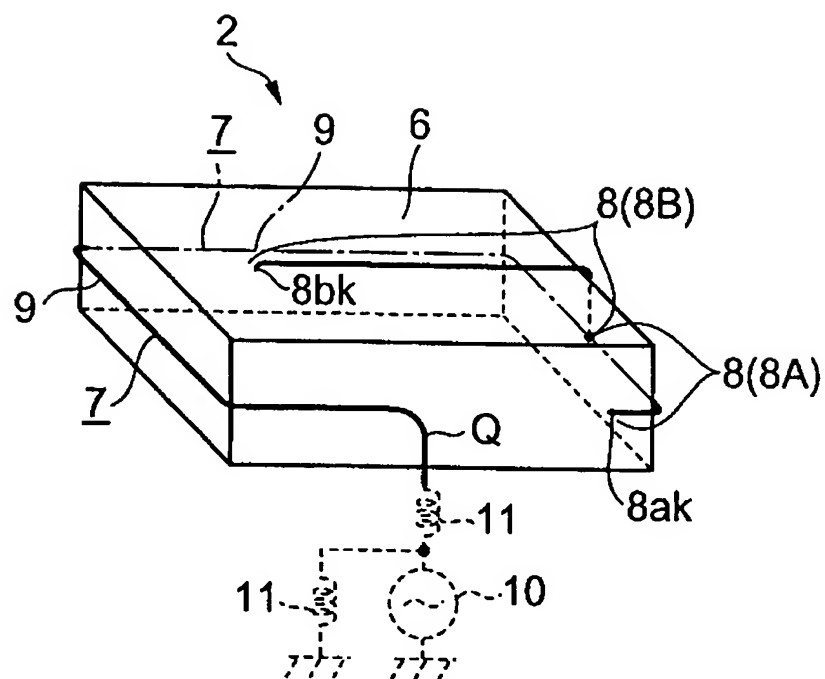


FIG. 3

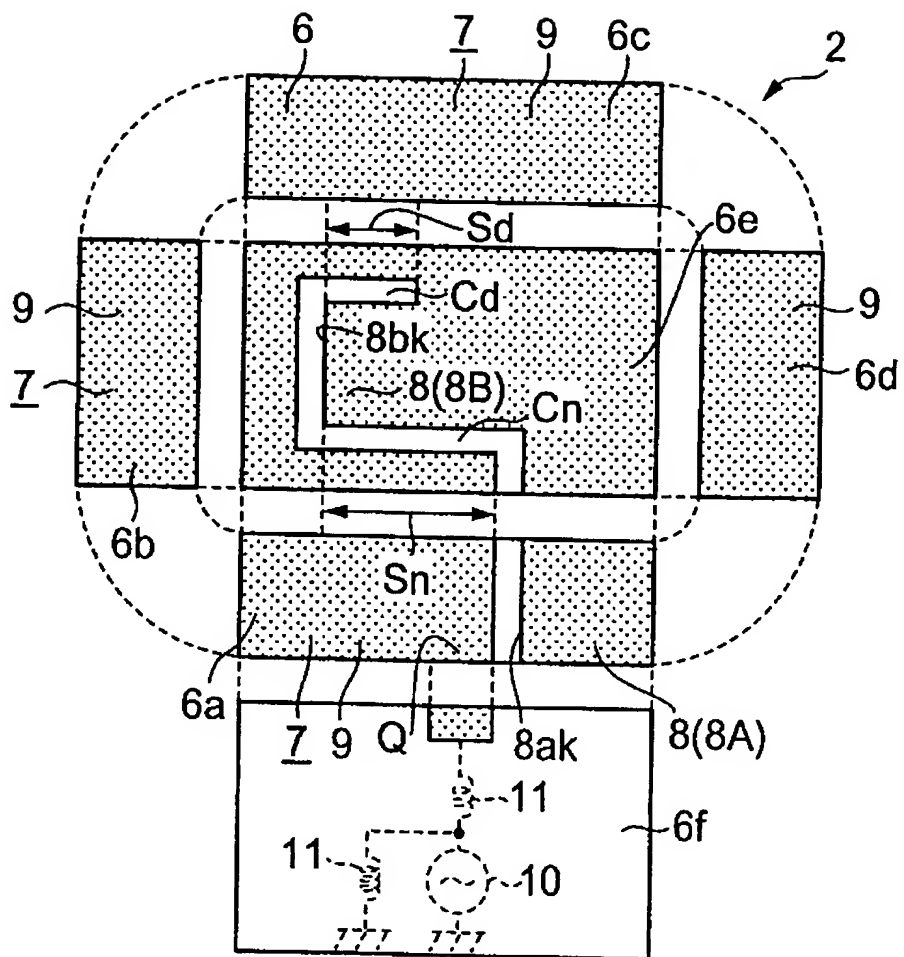


FIG. 5A

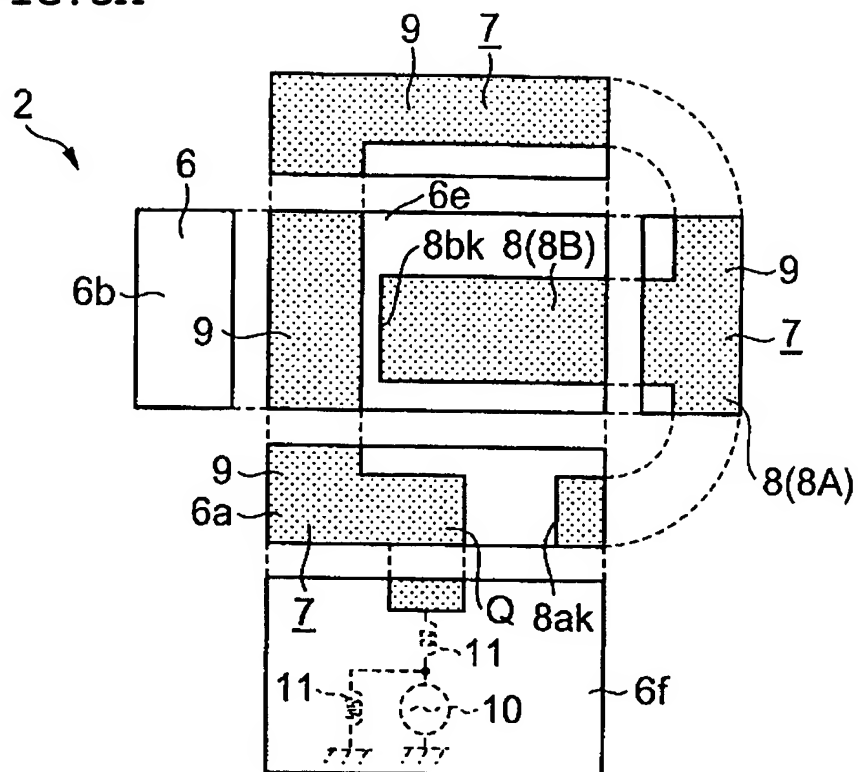


FIG. 5B

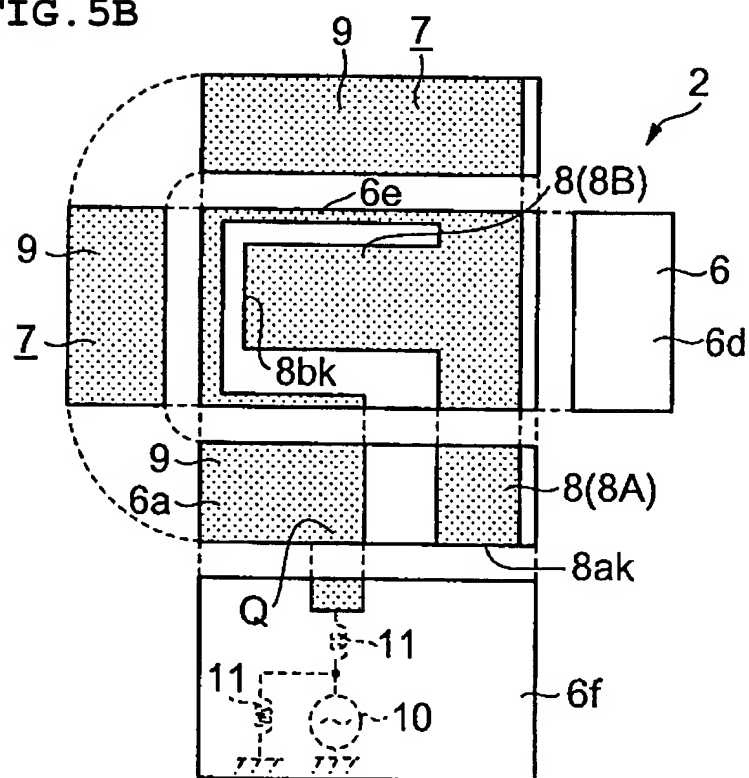


FIG. 8

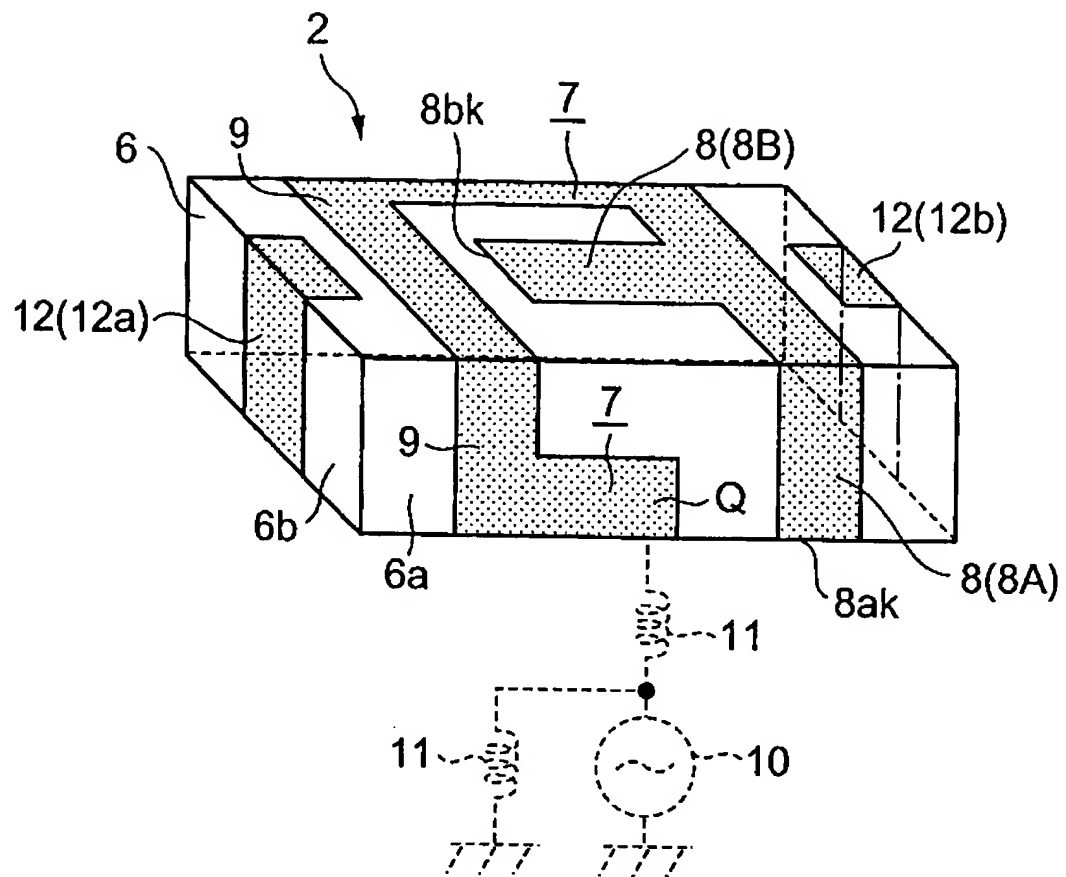


FIG. 9

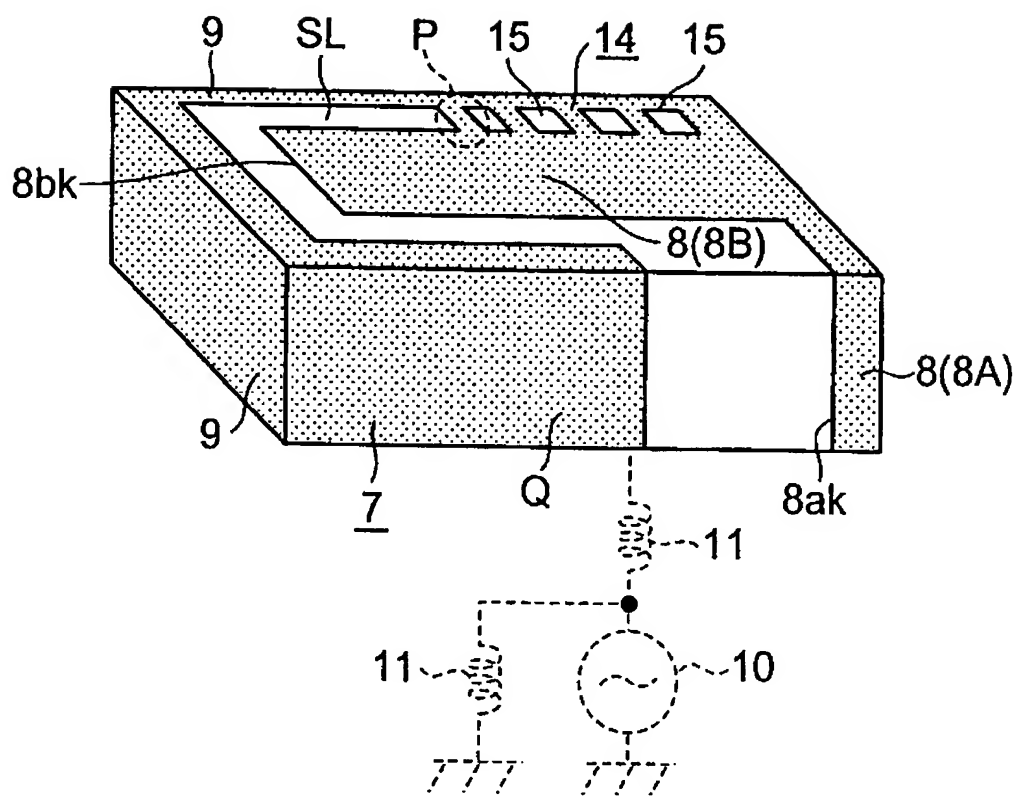


FIG. 10

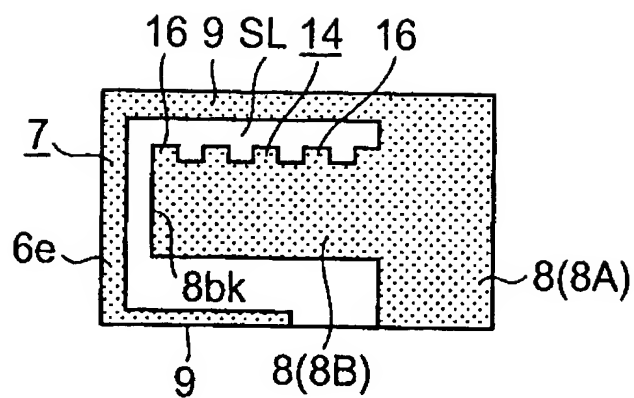


FIG. 11A

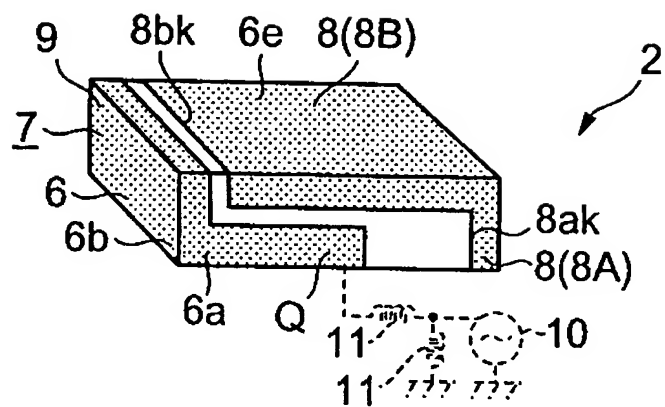


FIG. 11B

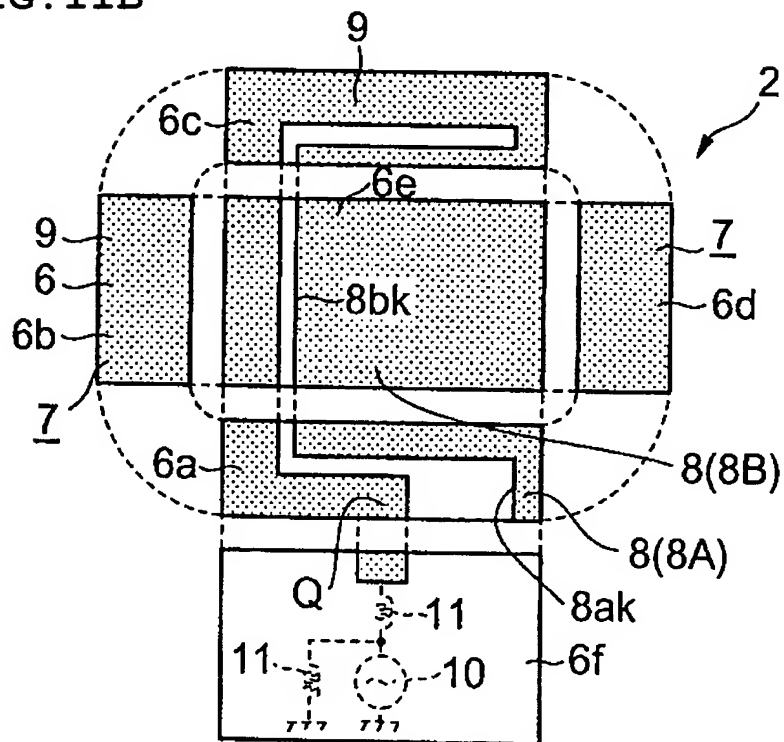


FIG. 12

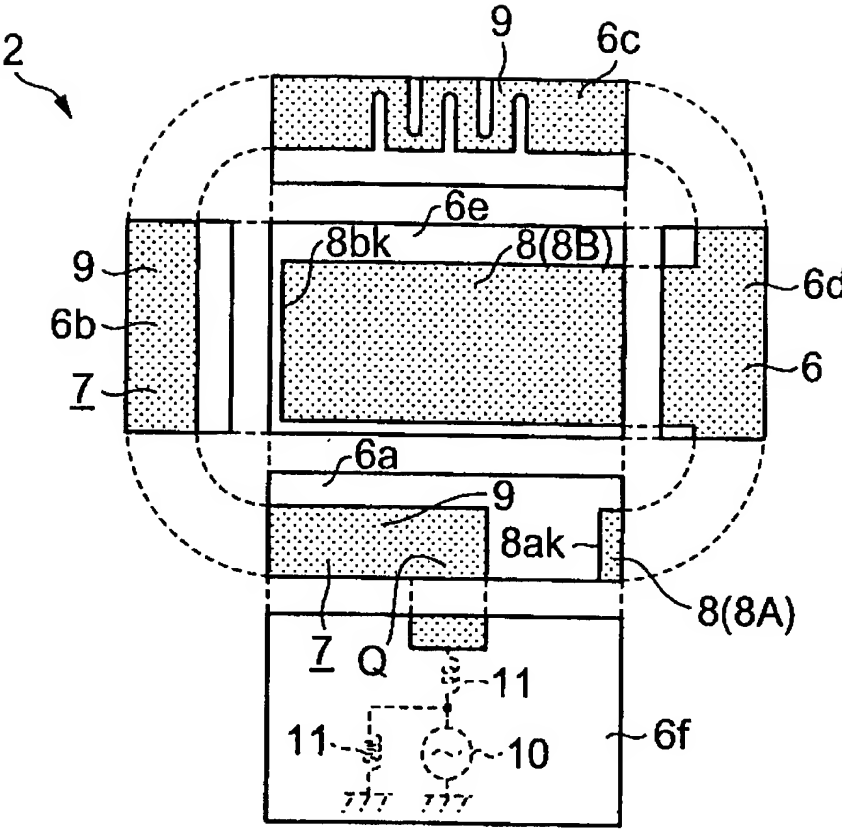


FIG. 13

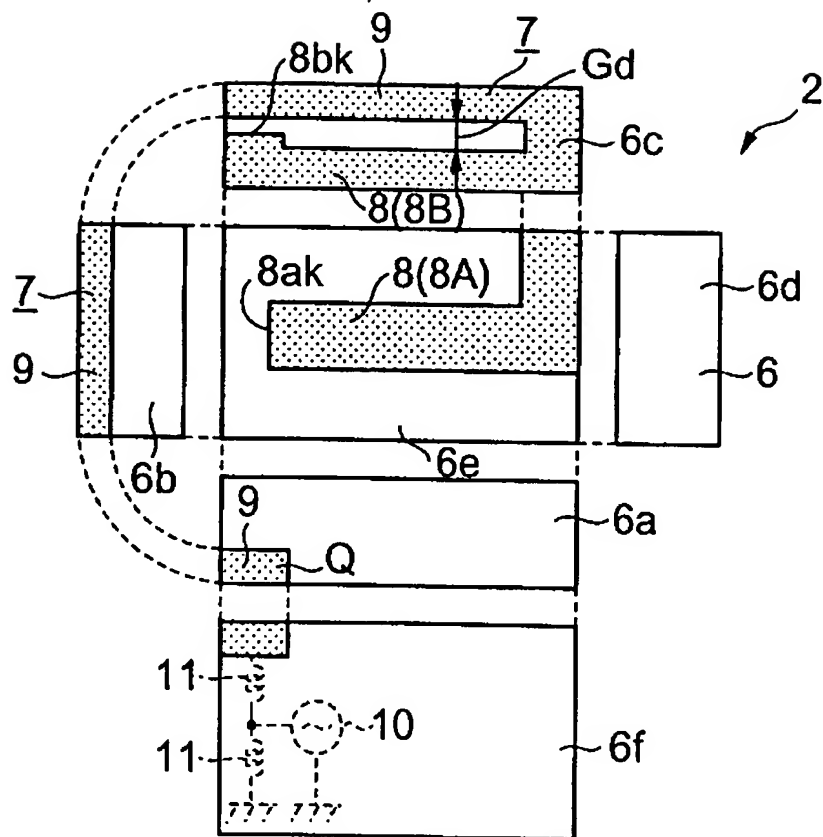


FIG. 15

